

isc N-Channel MOSFET Transistor

2SK1649

DESCRIPTION

- Drain Current –I_D=6A@ T_C=25 $^\circ\!\!\mathrm{C}$
- Drain Source Voltage-
- : V_{DSS}=900 (Min)
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- high speed high current switching applications
- DC-DC converter and motor driver applications

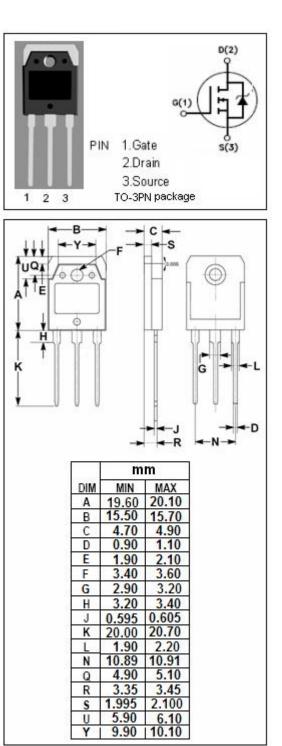
SYMBOL	ARAMETER	VALUE	UNI T			
V _{DSS}	Drain-Source Voltage (V _{GS} =0)	900	V			
V _{GS}	Gate-Source Voltage	±30	V			
ID	Drain Current-continuous@ TC=25°C	6	А			
P _{tot}	Total Dissipation@TC=25℃	150	w			
Tj	Max. Operating Junction Temperature	150	°C			
T _{stg}	Storage Temperature Range	-55~150	°C			

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
Rth j-c	Thermal Resistance, Junction to Case	1.0	°C/W
Rth j-a	Thermal Resistance, Junction to Ambient	83.3	°C/W

1





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ELECTRICAL CHARACTERISTICS (TC-25 C)								
PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT			
Drain-Source Breakdown Voltage	V _{GS} =0; I _D = 10mA	900			V			
Gate Threshold Voltage	V _{DS} =10V; I _D =1mA	1.5		3.5	V			
Drain-Source On-stage Resistance	V _{GS} =10V; I _D =3A			2.5	Ω			
Gate Source Leakage Current	V _{GS} = ±25V;V _{DS} = 0			±100	nA			
Zero Gate Voltage Drain Current	V _{DS} =720V; V _{GS} = 0			300	uA			
Diode Forward Voltage	I _F =6A; V _{GS} =0			2.0	V			
	PARAMETER Drain-Source Breakdown Voltage Gate Threshold Voltage Drain-Source On-stage Resistance Gate Source Leakage Current Zero Gate Voltage Drain Current	PARAMETERCONDITIONSDrain-Source Breakdown VoltageVGS=0; ID= 10mAGate Threshold VoltageVDS=10V; ID=1mADrain-Source On-stage ResistanceVGS=10V; ID=3AGate Source Leakage CurrentVGS= ±25V; VDS= 0Zero Gate Voltage Drain CurrentVDS=720V; VGS= 0	PARAMETERCONDITIONSMINDrain-Source Breakdown Voltage $V_{GS}=0$; $I_D=10mA$ 900Gate Threshold Voltage $V_{DS}=10V$; $I_D=1mA$ 1.5Drain-Source On-stage Resistance $V_{GS}=10V$; $I_D=3A$ 1.5Gate Source Leakage Current $V_{GS}=\pm 25V$; $V_{DS}=0$ 2ero Gate Voltage Drain Current $V_{DS}=720V$; $V_{GS}=0$	PARAMETERCONDITIONSMINTYPDrain-Source Breakdown Voltage $V_{GS}=0$; $I_D=10mA$ 900Gate Threshold Voltage $V_{DS}=10V$; $I_D=1mA$ 1.5Drain-Source On-stage Resistance $V_{GS}=10V$; $I_D=3A$ 1.5Gate Source Leakage Current $V_{GS}=\pm25V$; $V_{DS}=0$ 1.5Zero Gate Voltage Drain Current $V_{DS}=720V$; $V_{GS}=0$ 1.5	PARAMETERCONDITIONSMINTYPMAXDrain-Source Breakdown Voltage $V_{GS}=0; I_D=10mA$ 900Gate Threshold Voltage $V_{DS}=10V; I_D=1mA$ 1.53.5Drain-Source On-stage Resistance $V_{GS}=10V; I_D=3A$ 2.5Gate Source Leakage Current $V_{GS}=\pm 25V; V_{DS}=0$ ± 100 Zero Gate Voltage Drain Current $V_{DS}=720V; V_{GS}=0$ 300			

• ELECTRICAL CHARACTERISTICS (Tc=25°C)

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2